MSKSEMI 美森科













ESD

SS

MOV

GDI

PLED

MURSXXXT3G-MS

Product specification





SURFACE MOUNT ULTRAFAST POWER RECTIFIERS DIODES

VOLTAGE RANGE: 50 - 600V

CURRENT: 1.0A

Features

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Voltage Drop, High Efficiency
- Low Power Loss
- Super-Fast Recovery Time
- Plastic Case Material has UL Flammability Classification Rating 94V-O

Mechanical Data

- Case: SMA/DO-214AA, Molded Plastic
- Terminals: Solder Plated, Solderable
- per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Weight: 0.093 grams (approx.)

Reference News

PACKAGE OUTLINE	Marking
A STATE OF THE PARTY OF THE PAR	MURS ***
SMB(DO-214AA)	*** Representative VRRM



Maximum Ratings and Electrical Characteristics TA = 25℃ unless otherwise specified Single

phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

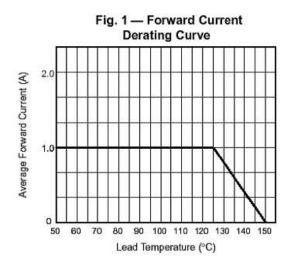
Characteristic		Symbol			MURS115 T3G-MS			MURS140 T3G-MS	MURS160 T3G-MS	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		VRRM VRWM VR	50	100	150	200	300	400	600	V
RMS Reverse Voltage		VR(RMS)	35	70	105	140	210	280	420	V
Average Rectified Output Current	TL = 150 °C TL = 125 °C	lo	1.0 2.0			Α				
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)		IFSM	40 35				Α			
Forward Voltage @I _F = 1.0A		VFM	0.875 1.25				V			
Peak Reverse Current At Rated DC Blocking Voltage	@T _A = 25°C @T _A = 100°C	lгм	10.0 150				μΑ			
Reverse Recovery Time (Note 1)		trr	35					nS		
Typical Junction Capacitance (Note 2)		Cj	25					pF		
Typical Thermal Resistance (Note 3)		Røjl	13					°C/W		
Operating and Storage Temperature Range		Т _{ј,} Тsтg	-65 to +150					°C		

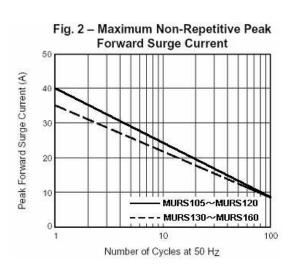
Note:1.Reverse recovery condition IF=0.5A,IR=1.0A,Irr=0.25A 2.Measured at 1MHz and applied reverse voltage of 4.0V D.C.

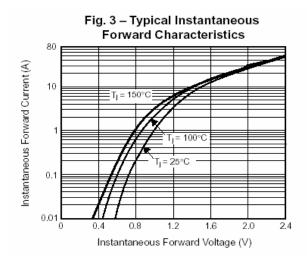
^{3.}P.C.B. mounted with 0.2x0.2"(5.0x5.0mm) copper pad areas

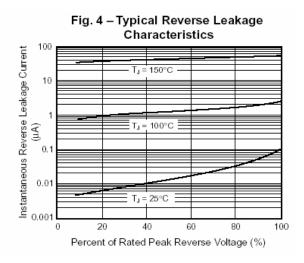


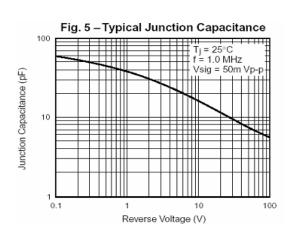
RATINGS AND CHARAC TERISTIC MURVES MURSXXXT3G-MS





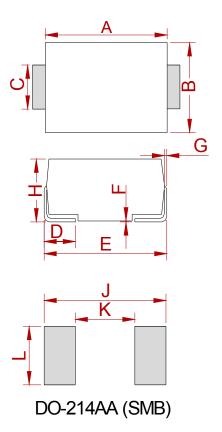








PACKAGE MECHANICAL DATA



	Dimensions				
Ref. Mill		neters	Inches		
	Min.	Max.	Min.	Max.	
Α	4.25	4.75	0.167	0.187	
В	3.30	3.94	0.130	0.155	
С	1.85	2.21	0.073	0.087	
D	0.76	1.52	0.030	0.060	
Е	5.08	5.59	0.200	0.220	
F	0.051	0.203	0.002	0.008	
G	0.15	0.31	0.006	0.012	
Н	2.11	2.44	0.083	0.096	
J	6.80		0.270		
K		2.60		0.100	
L	2.40		0.090		

REEL SPECIFICATION

P/N	PKG	QTY
MURSXXXT3G-MS	DO-214AA(SMB)	2500



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